

Process Details

| | |
|------------------------|-------------------------|
| Wafer Size | 5" |
| PDPW(pcs/Wafer) | 10860 pcs/wafer |
| Chip Size(La) | 1000um*1000um |
| Pad size(Lb) | 830um*830um |
| Die Thickness | 250±20um |
| Top Side Metalization | Ag:3.0um |
| Back Side Metalization | Ag: 1.5um |
| Passivation layer | SiO ₂ :1.0um |
| Street Size | 50um |



Maximum Ratings (Rating at 25°C ambient temperature unless otherwise specified)

| Item | Symbol | Value | Unit |
|-----------------------|------------------|-------------|------|
| Operating Temperature | T _J | 175 | °C |
| Storage Temperature | T _{STG} | -30 to +150 | °C |

Electrical Characteristics ((Rating at 25°C ambient temperature unless otherwise specified))

| Part No. | V _Z (V) | @I _{ZT} =mA | Z _{ZK} (Ω) | Z _{ZT} (Ω) | @I _{ZT} =mA | I _R (uA) | V _R (V) |
|-------------------|--------------------|----------------------|-----------------------|---------------------|----------------------|---------------------|--------------------|
| | | | @I _{ZK} =1mA |) | | Max. | |
| GDZ2CW100200YY-CS | 19.00~21.00 | 65 | 75 | 3.5 | 50 | 0.5 | 16.7 |